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(71) Applicant (for all designated States except US): **BATTELLE MEMORIAL INSTITUTE** [US/US]; 902 Battelle Boulevard, P.O. Box 999, Richland, WA 99352 (US).

(72) Inventors; and

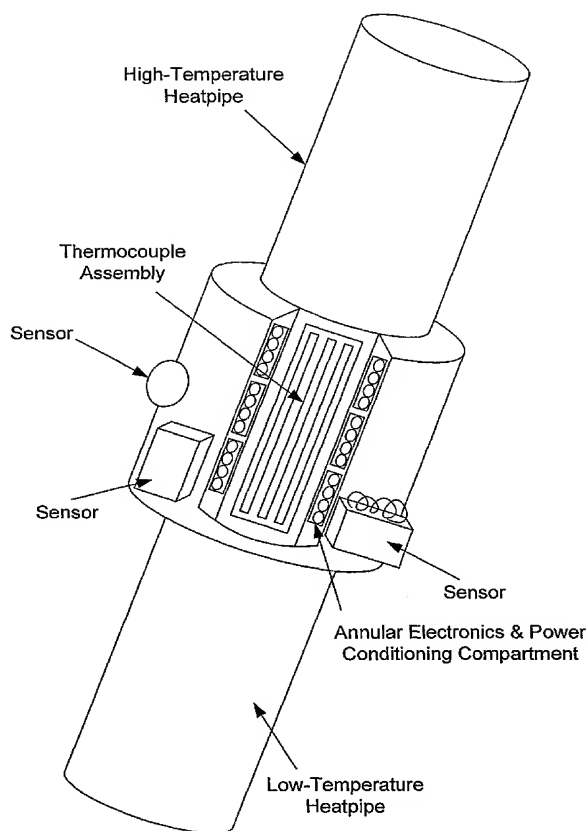
(75) Inventors/Applicants (for US only): **OLSEN, Larry, C.** [US/US]; 490 Clermont Drive, Richland, WA 99352 (US). **DESTEESE, John, G.** [US/US]; 3323 West Canal Drive, Kennewick, WA 99336 (US). **MARTIN, Peter, M.** [US/US]; 7703 West 13th Avenue, Kennewick, WA 99338 (US). **JOHNSTON, John, W.** [US/US]; 111 Shad-bolt, Yakima, WA 98908 (US). **PETERS, Timothy, J.** [US/US]; 1845 Alder Avenue, Richland, WA 99352 (US).

(74) Agent: **CALDWELL, Lisa, M.**; Klarquist Sparkman, LLP, One World Trade Center, Suite 1600, 121 S.W. Salmon Street, Portland, OR 97204 (US).

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[Continued on next page]

(54) Title: THERMOELECTRIC DEVICES AND APPLICATIONS FOR THE SAME



(57) Abstract: High performance thin film thermoelectric couples and methods of making the same are disclosed. Such couples allow fabrication of at least microwatt to watt-level power supply devices operating at voltages greater than one volt even when activated by only small temperature differences.

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